

PHYSICAL REVIEW B

For editorial and subscription correspondence,
please see inside front cover
(ISSN: 0163-1829)

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American Institute of Physics
500 Sunnyside Boulevard
Woodbury, NY 11797-2999

THIRD SERIES, VOLUME 57, NUMBER 23

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15 JUNE 1998-I

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0163-1829(19980615)57:23;1-Q